

# Fast recovery Diode

## RF103L2S

### ●Applications

High frequency rectification

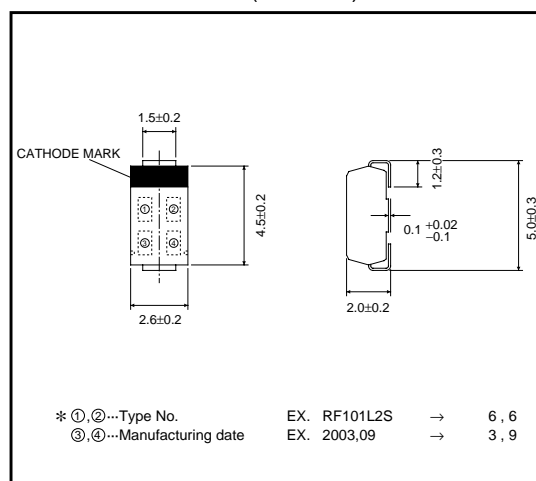
### ●Features

- 1) Small power mold type (PMDS)
- 2) Ultra low VF
- 3) Very fast recovery
- 4) Low switching loss

### ●Construction

Silicon epitaxial planar

### ●External dimensions (Unit : mm)



### ●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	$V_{RM}$	200	V
Reverse voltage (DC)	$V_R$	200	V
Average rectified forward current *	$I_o$	1.0	A
Forward Peak surge current (60Hz· 1cyc.)	$I_{FSM}$	20	A
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-40 to +150	°C

\* Mounting on glass epoxy board

### ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Typ.	Max.	Unit	Conditions
Forward voltage	$V_F$	0.860	0.920	V	$I_F=1.0A$
Reverse current	$I_R$	1.2	10	$\mu A$	$V_R=200V$
Reverse recovery time	$t_{rr}$	9	20	nS	$I_F=0.5A$
					$I_R=1.0A$
					$I_{rr}=0.25 \times I_R$

Diodes

●Electrical characteristic curves (Ta=25°C)

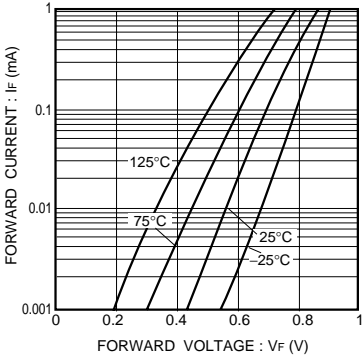


Fig.1 Forward temperature characteristics

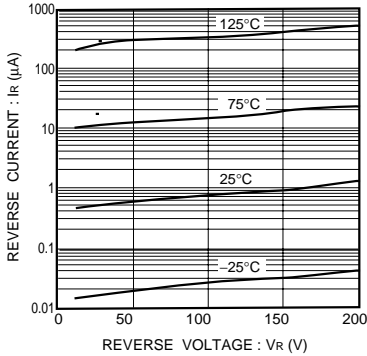


Fig.2 Reverse temperature characteristics

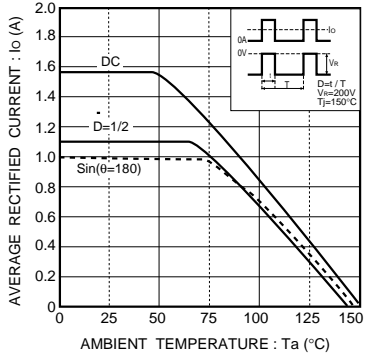


Fig.3 Derating curve

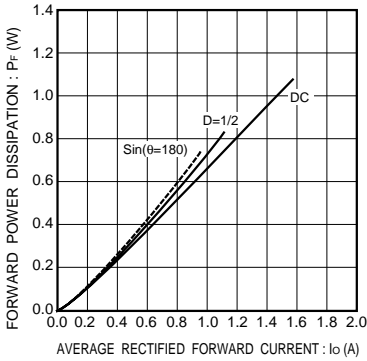


Fig. 4 Power dissipation characteristics

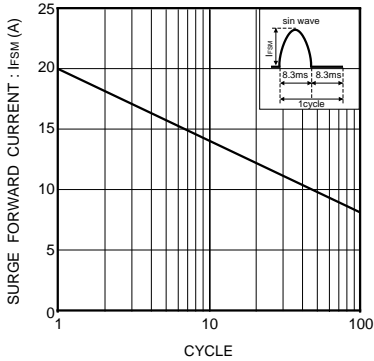


Fig.5 Power peak surge current

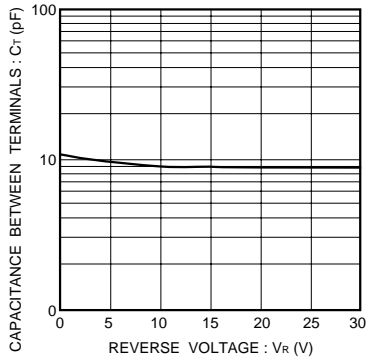


Fig. 6 Capacitance between terminals characteristics

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